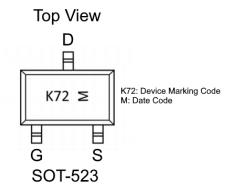
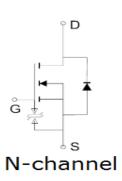


General Description

The FX2N7002KMFH-06S1G is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching, and low in-line power loss are needed in a very small outline surface mount package.

PIN Configuration





Features

- RDS(ON) \leq 3Ω@VGS=10V
- RDS(ON) \leq 4Ω@VGS=4.5V
- ESD Protection HBM >2KV
- Super high density cell design for extremely low RDS(ON)
- Exceptional on-resistance and maximum DC current capability

Applications

- Power Management in Note book
- DC/DC Converter
- Load Switch
- LCD Display inverter

Absolute Maximum Ratings(TA=25oC Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit	
Drain-Source Voltage		VDS	60	V	
Gate-Source Voltage		Vgs	±20	V	
Continuous Drain	Ta=25°C	lo	0.27	A	
	Ta=70°C	ΙD	0.21		
Pulsed Drain Current		Ідм	1.07	А	
Maximum Power Dissipation	Ta=25°C	PD	0.34	W	
	Ta=70°C	PD	0.22		
Operating Junction Temperature		TJ	-55 to 150	$^{\circ}\!\mathbb{C}$	
Thermal Resistance-Junction to Ambient*		RθJA	367	°C/W	

^{*} The device mounted on 1in² FR4 board with 2 oz copper



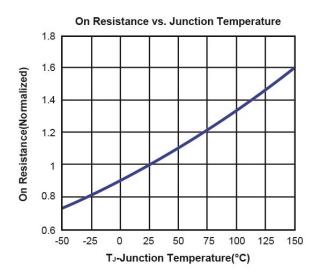
Electrical Characteristics (TA =25 $^{\circ}$ Unless Otherwise Specified)

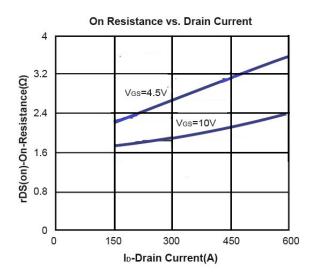
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
STATIC		<u> </u>			1		
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0, I _D =10uA	60			V	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1.3		2.1	V	
Igss	Gate Body Leakage	V _{GS} = ±20V , V _{DS} =0V			±10	uA	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V			1	uA	
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =500mA			3	Ω	
		V _{GS} =4.5V, I _D =200mA			4	12	
V _{SD}	Diode Forward Voltage	Is=200mA, V _{GS} =0V			1.2	V	
Dynam	ic	<u> </u>	•		1	,	
Qg	Total Gate Charge	VDS=30V,VGS=10V,ID=200mA		3.7		nC	
Qg	Total Gate Charge			1.4			
Qgs	Gate-Source Charge	VDS=30V,VGS=4.5V,ID=200mA		2.2			
Qgd	Gate-Drain Charge			0.2			
Ciss	Input Capacitance			21		pF	
Coss	Output Capacitance	VDS=25V, VGS=0V, f=1MHz		3			
Crss	Reverse Transfer Capacitance			1			
td(on)	Turn-On Delay Time	VD0 00V DI 4500		3.5		- Ns	
tr	Turn-On Rise Time	VDS=30V, RL =150Ω		20.3			
td(off)	Turn-Off Delay Time	VGS=10V,RGS=10Ω		4.4			
t f	Turn-Off Fall Time	— ID=200mA		22.2			

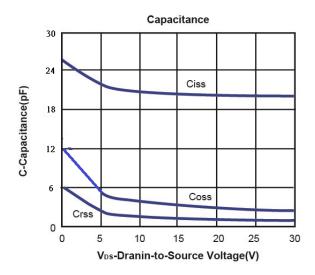
Notes : a. Pulse test: pulse width \leq 300us, duty cycle \leq 2%, Guaranteed by design, not subject to production testing.

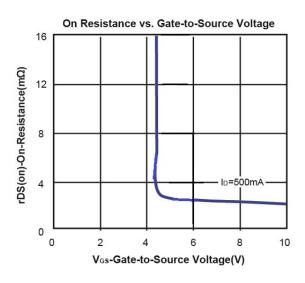
b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

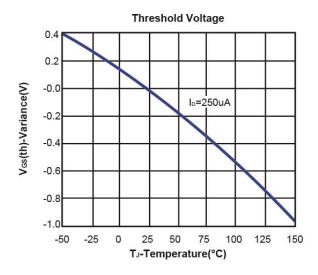
Typical Characteristics (TJ = 25° C Noted)

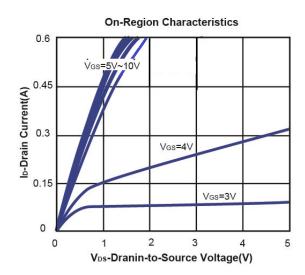




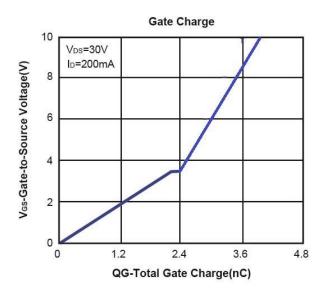


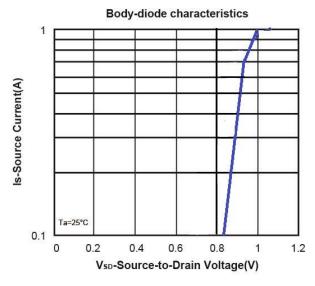


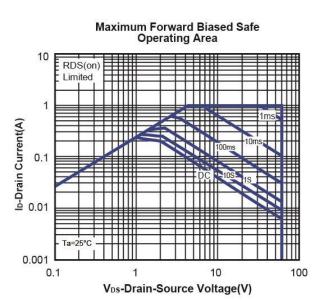


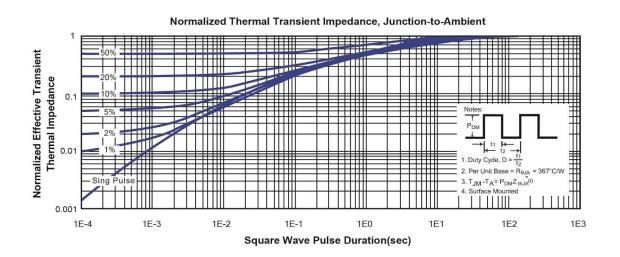




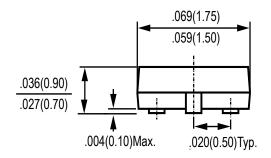


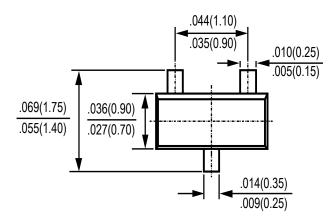


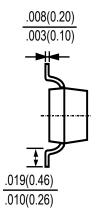




Package Outline Dimensions







SOT-523
Dimensions in inches and (millimeters)



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